Most Frequently Occurring Classifications of Patents Returned From A Search of 10/750,045 on November 03, 2005

Combined Classifications

18 136/258	
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12 257/E21.101

7 257/56

7 257/E21.133

6 257/55

5 136/249

5 427/578

5 438/485

5 438/96

4 204/192.25

4 257/E21.413

4 257/E21.414

4 257/E21.703

4 438/166

3 136/255

3 257/76

3 257/E29.003

3 257/E29.293

3 365/113

3 427/74

3 438/479

3 438/487

3 438/488

2 117/8

2 117/929

2 204/192.26

2 252/501.1

2 252/62.3R

2 257/22

2 257/458

2 257/53

2 257/54

2 257/58 2 257/66

2 257/72

2 257/E21.102

2 257/E27.111

2 257/E29.083

2 257/E29.151 2 257/E29.294

2 257/E33.025

2 257/E45.002

2 313/311

2 313/495

2 346/135.1

2 420/578

2 420/903

2 427/527

2 427/554

2 428/408

2 429/111

2 430/270.12

2 430/84

2 430/945

2 438/105

2 438/46

2 438/486

2 438/503

2 438/74

From A Search of 10/750,045 on November 03, 2005

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18 136/258
               (3 OR, 15 XR)
     Class 136: BATTERIES: THERMOELECTRIC AND PHOTOELECTRIC
     136/243
                     PHOTOELECTRIC
     136/252
                     .Cells
     136/258
                     ..Polycrystalline or amorphous semiconductor
 7 257/56
              (2 OR, 5 XR)
     Class 257: ACTIVE SOLID-STATE DEVICES
     257/49
                      NON-SINGLE CRYSTAL, OR RECRYSTALLIZED,
                 SEMICONDUCTOR MATERIAL FORMS PART OF ACTIVE JUNCTION
                (INCLUDING FIELD-INDUCED ACTIVE JUNCTION)
     257/52
                      .Amorphous semiconductor material
     257/53
                      ..Responsive to nonelectrical external signals
               (e.a., light)
     257/56
                      ...With impurity other than hydrogen to
               passivate dangling bonds (e.g., halide)
 7 257/E21.133 (0 OR, 7 XR)
     Class 257: ACTIVE SOLID-STATE DEVICES
     257/E21.001
                      PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE
                  OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE DEVICES OR
OF
                  PARTS THEREOF (EPO)
     257/E21.002
                      .Manufacture or treatment of semiconductor
                 device (EPO)
     257/E21.04
                     .. Device having at least one potential-jump
                barrier or surface barrier, e.g., PN junction, depletion
                layer, carrier concentration layer (EPO)
     257/E21.085
                     ...Device having semiconductor body comprising
                Group IV elements or Group III-V compounds with or without
                impurities, e.g., doping materials (EPO)
                      ....Deposition of semiconductor material on
     257/E21.09
               substrate, e.g., epitaxial growth, solid phase epitaxy
                (EPO)
                      .....Epitaxial re-growth of non-monocrystalline
     257/E21.133
               semiconductor material, e.g., lateral epitaxy by seeded
               solidific ation, solid-state crystallization, solid-state
               graphoepitaxy, explosive crystallization, grain growth in
               polycrystalline material (EPO)
 6 257/55
              (0 OR, 6 XR)
     Class 257: ACTIVE SOLID-STATE DEVICES
     257/49
                      NON-SINGLE CRYSTAL, OR RECRYSTALLIZED,
                 SEMICONDUCTOR MATERIAL FORMS PART OF ACTIVE JUNCTION
                (INCLUDING FIELD-INDUCED ACTIVE JUNCTION)
     257/52
                      .Amorphous semiconductor material
     257/53
                      .. Responsive to nonelectrical external signals
                (e.g., light)
     257/55
                      ... Amorphous semiconductor is alloy or contains
               material to change band gap (e.g., Si x Ge 1-x, SiN y)
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5 136/249 (2 OR, 3 XR)

Class 136: BATTERIES: THERMOELECTRIC AND PHOTOELECTRIC

136/243 PHOTOELECTRIC

136/244 .Panel or array

136/249 ... Monolithic semiconductor

5 427/578 (0 OR, 5 XR)

Class 427: COATING PROCESSES

427/457 DIRECT APPLICATION OF ELECTRICAL, MAGNETIC,

WAVE, OR PARTICULATE ENERGY

427/569 .Plasma (e.g., corona, glow discharge, cold

plasma, etc.)

427/578 ... Silicon containing coating material

5 438/485 (3 OR, 2 XR)

Class 438: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/478 FORMATION OF SEMICONDUCTIVE ACTIVE REGION ON

ANY SUBSTRATE (E.G., FLUID GROWTH, DEPOSITION)

438/482 .Amorphous semiconductor

438/485 ... Deposition utilizing plasma (e.g., glow

discharge, etc.)

5 438/96 (1 OR, 4 XR)

Class 438: SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

438/51 ...Packaging (e.g., with mounting,

encapsulating, etc.) or treatment of packaged

semiconductor

438/57 .Responsive to electromagnetic radiation

438/96 ... Amorphous semiconductor

From A Search of 10/750,045 on November 03, 2005

PLUS Search Results for S/N 10/750,045, Searched November 03, 2005 (top 50)

The Patent Linguistics Utility System (PLUS) is a USPTO automated search system for U.S. Patents from 1971 to the present. PLUS is a query-by-example search system which produces a list of patents that are most closely related linguistically to the application searched. This search was prepared by the staff of the Scientific and Technical Information Center, SIRA:

5294518	5783838	5725674	6475840	4485389
5440507	5932893	5736431	6548380	4508931
6319761	6077722	6100465	6846728	4511638
6335542	6099918	6165841	4925700	4520380
5488000	4855249	6218771	5652067	4522663
4332833	4857415	6218771	4342044	4600801
4352239	5371383	6259191	4365107	4605941
4441973	5374318	6288325	4409605	4624862
5192393	5633192	6391690	4451538	4756924
5194349	5682041	6407012	4463028	4769682